

P-Channel MOSFET MEM2301XG-N

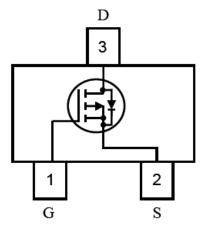
General Description

MEM2301XG-N Series P-channel enhancement mode field-effect transistor, These miniature surface mount MOSFETs utilize High Cell Density process. Low RDS(ON) assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are lower voltage application, power management in portable and battery-powered products such as computers, printers, and PCMCIA cards, cellular and cordless telephones.

Features

- -20V/-2.8A RDS(ON), Vgs@-1.8V, Ids@-1.1A = 230mΩ RDS(ON), Vgs@-2.5V, Ids@-2.0A = 140mΩ RDS(ON), Vgs@-4.5V, Ids@-3.1A = 96mΩ
- High Density Cell Design For Ultra Low On-Resistance
- Fast switching speed
- High performance trench technology
- Low thermal impedance copper lead frame
- Subminiature surface mount package:SOT23

Pin Configuration



Typical Application

- Power management
- Load switch
- Battery protection

Absolute Maximum Ratings (TA = 25° C unless otherwise noted)

Param	eter	Symbol	Ratings	Unit	
Drain-Source Voltage		V_{DSS}	-20	V	
Gate-Source Voltage		V_{GSS}	±12	V	
Continuous D	rain Current	I _D	-2.8	Α	
Pulsed Drain Current ^{1,2}		I _{DM}	-17	Α	
Total Power Dissipation	T _A =25°C	Б	1.4	١٨/	
	T _A =70°C	P_{D}	0.8	W	
Operating Temperature Range		T _{Opr}	-55~150	$^{\circ}$ C	
Storage Tempe	rature Range	T _{stg}	-55~150	$^{\circ}$	

Thermal Characteristics

Parameter	Symbol	MAX.	Unit
Thermal Resistance, Junction-to-Ambient ³	$R_{ heta JA}$	90	℃W

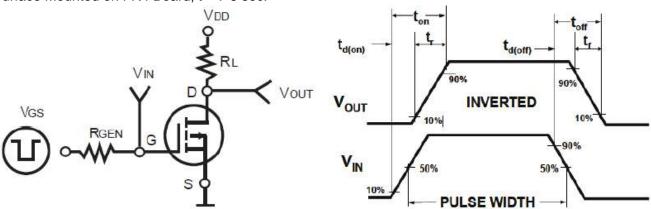


MEM2301XG-N

Electrical Characteristics

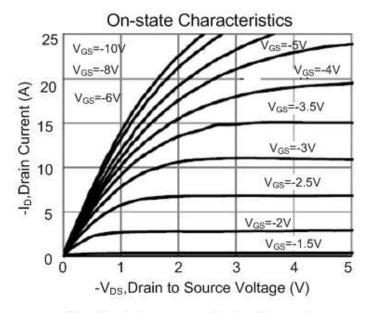
Parameter	Symbol	Test Condition	Min	Туре	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	-20	-23	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	-0.4	-0.72	-1.1	V
Gate-Body Leakage		V_{DS} =0V, V_{GS} =12V	-	-	100	nA
	I_{GSS}	V_{DS} =0 V , V_{GS} =-12 V	-	-	-100	nA
		V_{DS} =-20V V_{GS} =0V	-	-	-1.0	^
Zara Cata Valtaga Drain Current		$T_J=25^{\circ}C$	_	-	-1.0	μA
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-16 V_{GS} =0 V		-	-10	μΑ
		T _J =55°C	-			
	R _{DS(ON)1}	V_{GS} =-1.8 V , I_{D} =-1.1 A	-	230	260	mΩ
Static Drain-Source On-Resistance	R _{DS(ON)2}	V_{GS} =-2.5 V , I_{D} =-2.0 A	-	140	170	mΩ
	R _{DS(ON)3}	V_{GS} =-4.5 V , I_{D} =-2.8 A	-	98	130	mΩ
Forward Transconductance	g _{FS}	V_{DS} =-5 V , I_{D} =-1 A	3	5	-	S
Max. Diode Forward Current	Is		-	-	-2.8	Α
Source-drain (diode forward)	V_{SD}	V _{GS} =0V,I _S =-2.8A		-0.82	-1.2	V
voltage	VSD	V _{GS} =0V,I _S =-2.0A	_	-0.02	-1.2	V
Dynamic Characteristics						
Input Capacitance	Ciss	$V_{DS} = -10V$,	-	320	-	
Output Capacitance	Coss	$V_{GS} = 0 V$,	-	60	-	pF
Reverse Transfer Capacitance	Crss	f = 1 MHz	-	35	-	
Switching Characteristics						
Turn-On Delay Time	td(on)	$V_{DS} = -10 V$,	-	11	-	
Rise Time	tr	$I_D = -2.8 A$	-	5	-	no
Turn-Off Delay Time	td(off)	$V_{GS} = -4.5 V$,	-	22	-	ns
Fall-Time	tf	$Rg = 6 \Omega$	-	8	-	
Total Gate Charge	Qg	V _{DS} = -10 V,	-	3.2	-	
Gate-Source Charge	Qgs	$V_{GS} = -4.5 V$,	-	0.6	-	nc
Gate-Drain Charge	Qgd	$I_D = -2.0A$	-	0.9	-	

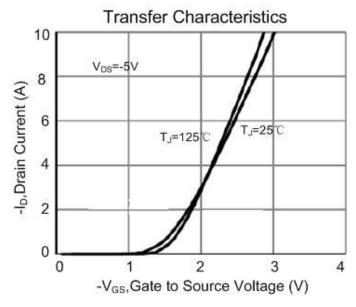
- 1. Pulse width limited by maximum junction temperature.
- 2. Pulse test: PW \leq 300 µs duty cycle \leq 2%.
- 3. Surface Mounted on FR4 Board, $t \leq 5$ sec.

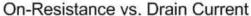


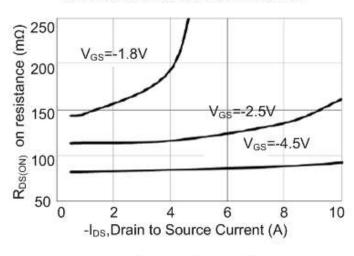


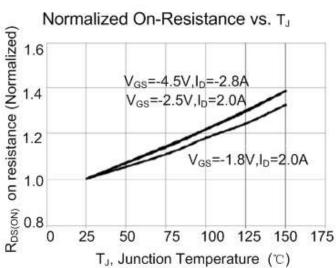
Typical Performance Characteristics

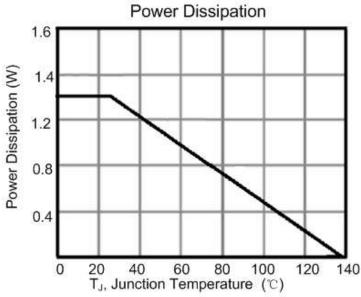


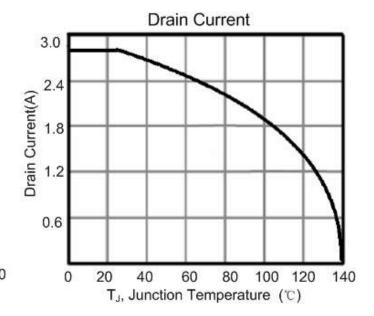






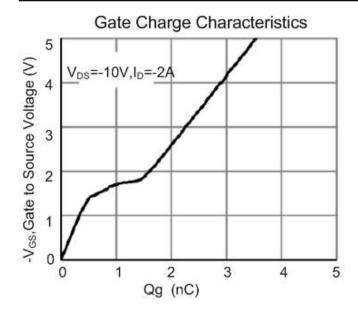


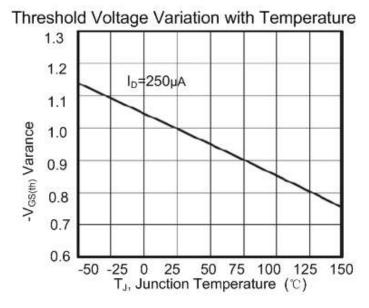


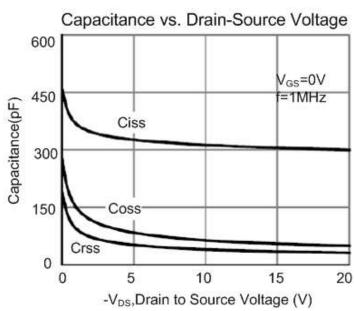


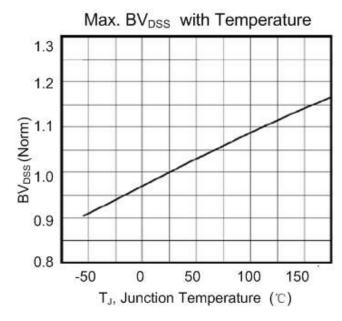


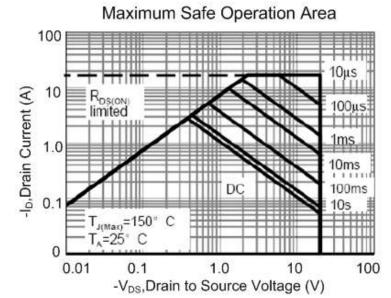








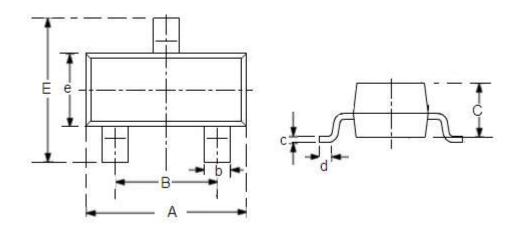






Package Information

Package Type:SOT23 Unit:mm(inch)



DIM	Millimeters		Inches		
	Min	Max	Min	Max	
А	2.7	3.1	0.1063	0.122	
В	1.7	2.1	0.0669	0.0827	
b	0.35	0.5	0.0138	0.0197	
С	1.0	1.2	0.0394	0.0472	
С	0.1	0.25	0.0039	0.0098	
d	0.2	-	0.0079	-	
E	2.1	2.64	0.0827	0.1039	
е	1.2	1.4	0.0472	0.0551	



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